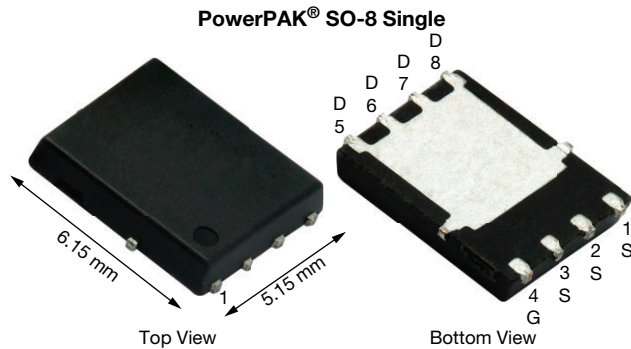


## P-Channel 30 V (D-S) MOSFET



PRODUCT SUMMARY	
$V_{DS}$ (V)	-30
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -10$ V	0.00170
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -4.5$ V	0.00265
$Q_g$ typ. (nC)	84
$I_D$ (A)	-195
Configuration	Single

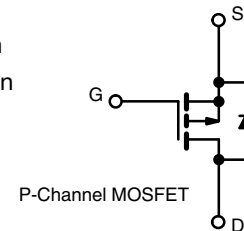
### FEATURES

- TrenchFET® Gen IV p-channel power MOSFET
- Very low  $R_{DS(on)}$  minimizes voltage drop and reduces conduction loss
- Eliminates the need for charge pump
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### APPLICATIONS

- Adapter and charger switch
- Battery and circuit protection
- OR-ing
- Load switch
- Motor drive control



ORDERING INFORMATION	
Package	PowerPAK SO-8
Lead (Pb)-free and halogen-free	SiRA99DP-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		$V_{DS}$	-30	V
Gate-source voltage		$V_{GS}$	+16 / -20	V
Continuous drain current ( $T_J = 150$ °C)	$T_C = 25$ °C	$I_D$	-195	A
	$T_C = 70$ °C		-156	
	$T_A = 25$ °C		-47.9 <sup>b, c</sup>	
	$T_A = 70$ °C		-38.3 <sup>b, c</sup>	
Pulsed drain current ( $t = 100$ $\mu$ s)		$I_{DM}$	-400	A
Continuous source-drain diode current	$T_C = 25$ °C	$I_S$	-94.5	A
	$T_A = 25$ °C		-5.6 <sup>b, c</sup>	
Single pulse avalanche current	L = 0.1 mH	$I_{AS}$	-50	mJ
Single pulse avalanche energy		$E_{AS}$	125	
Maximum power dissipation	$T_C = 25$ °C	$P_D$	104	W
	$T_C = 70$ °C		66.6	
	$T_A = 25$ °C		6.35 <sup>b, c</sup>	
	$T_A = 70$ °C		4 <sup>b, c</sup>	
Operating junction and storage temperature range		$T_J, T_{stg}$	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>c</sup>			260	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	$t \leq 10$ s	$R_{thJA}$	15	20	°C/W
Maximum junction-to-case (drain)	Steady state	$R_{thJC}$	0.9	1.2	

#### Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 54 °C/W
- $T_C = 25$  °C



SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT		
<b>Static</b>								
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = -250\text{ }\mu\text{A}$	-30	-	-	V		
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = -10\text{ mA}$	-	-14	-	mV/ $^\circ\text{C}$		
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = -250\text{ }\mu\text{A}$	-	6	-			
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\text{ }\mu\text{A}$	-1	-	-2.5	V		
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = +16 / -20\text{ V}$	-	-	100	nA		
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -30\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	-1	$\mu\text{A}$		
		$V_{DS} = -30\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 70\text{ }^\circ\text{C}$	-	-	-15			
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq -10\text{ V}$ , $V_{GS} = -10\text{ V}$	-40	-	-	A		
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$ , $I_D = -20\text{ A}$	-	0.00130	0.00170	$\Omega$		
		$V_{GS} = -4.5\text{ V}$ , $I_D = -15\text{ A}$	-	0.00220	0.00265			
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}$ , $I_D = -20\text{ A}$	-	114	-	S		
<b>Dynamic <sup>b</sup></b>								
Input capacitance	$C_{ISS}$	$V_{DS} = -15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	-	10 995	-	pF		
Output capacitance	$C_{OSS}$		-	5000	-			
Reverse transfer capacitance	$C_{RSS}$		-	510	-			
Total gate charge	$Q_g$	$V_{DS} = -15\text{ V}$ , $V_{GS} = -10\text{ V}$ , $I_D = -20\text{ A}$	-	172.5	260	nC		
		$V_{DS} = -15\text{ V}$ , $V_{GS} = -4.5\text{ V}$ , $I_D = -20\text{ A}$	-	84	126			
Gate-source charge	$Q_{gs}$	$V_{DS} = -15\text{ V}$ , $V_{GS} = -4.5\text{ V}$ , $I_D = -20\text{ A}$	-	35.6	-	-		
Gate-drain charge	$Q_{gd}$		-	27.5	-			
Gate resistance	$R_g$	$f = 1\text{ MHz}$	0.5	1.3	2.2	$\Omega$		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -15\text{ V}$ , $R_L = 0.75\text{ }\Omega$ , $I_D \cong -20\text{ A}$ , $V_{GEN} = -10\text{ V}$ , $R_g = 1\text{ }\Omega$	-	23	46	ns		
Rise time	$t_r$		-	19	38			
Turn-off delay time	$t_{d(off)}$		-	64	128			
Fall time	$t_f$		-	16	32			
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -15\text{ V}$ , $R_L = 0.75\text{ }\Omega$ , $I_D \cong -20\text{ A}$ , $V_{GEN} = -4.5\text{ V}$ , $R_g = 1\text{ }\Omega$	-	69	138	ns		
			Rise time	$t_r$	-		183	366
			Turn-off delay time	$t_{d(off)}$	-		51	102
			Fall time	$t_f$	-		57	114
<b>Drain-Source Body Diode Characteristics</b>								
Continuous source-drain diode current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	-	-	-94.5	A		
Pulse diode forward current	$I_{SM}$		-	-	-400			
Body diode voltage	$V_{SD}$	$I_S = -5\text{ A}$ , $V_{GS} = 0\text{ V}$	-	-0.71	-1.1	V		
Body diode reverse recovery time	$t_{rr}$	$I_F = -20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $T_J = 25\text{ }^\circ\text{C}$	-	75	150	ns		
Body diode reverse recovery charge	$Q_{rr}$		-	125	250	nC		
Reverse recovery fall time	$t_a$		-	31	-	ns		
Reverse recovery rise time	$t_b$		-	39	-			

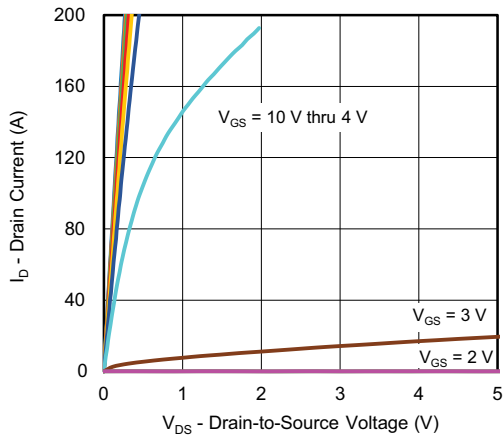
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

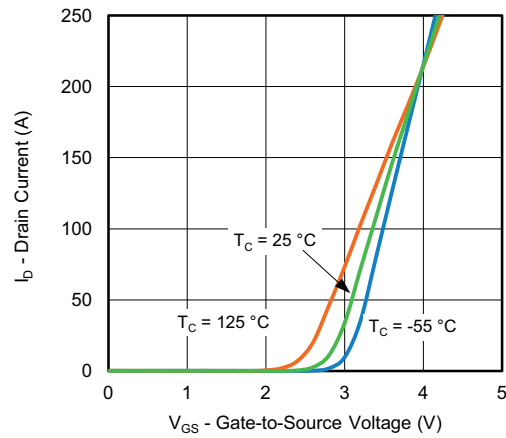
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.



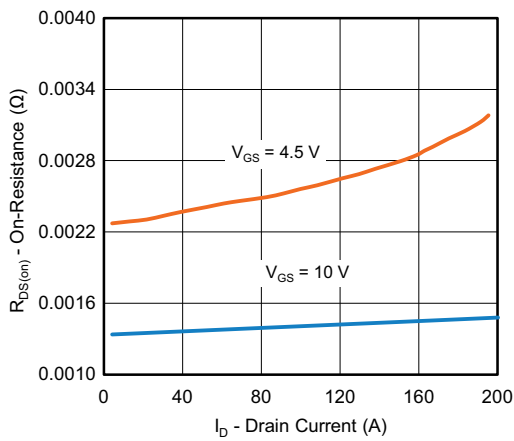
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



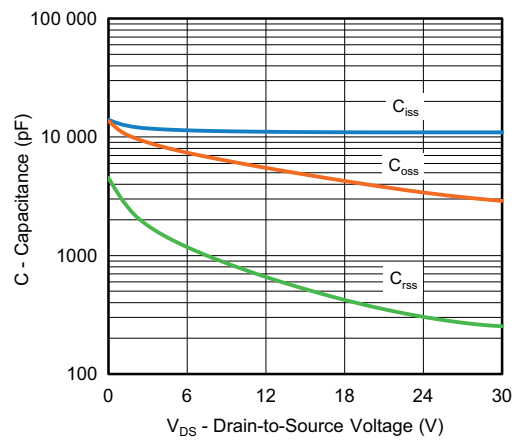
Output Characteristics



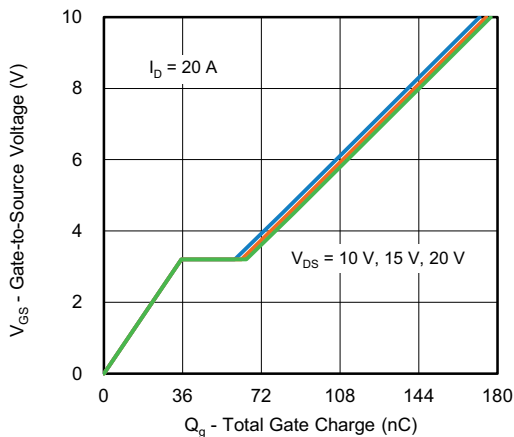
Transfer Characteristics



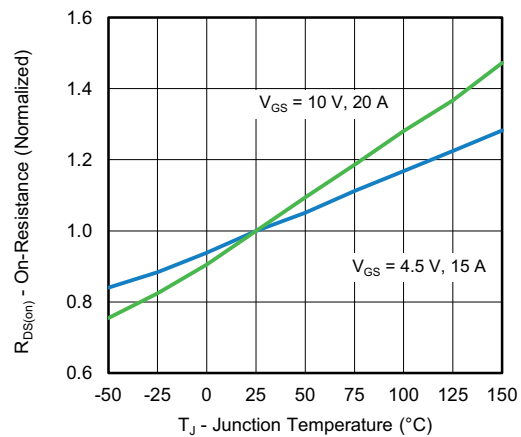
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



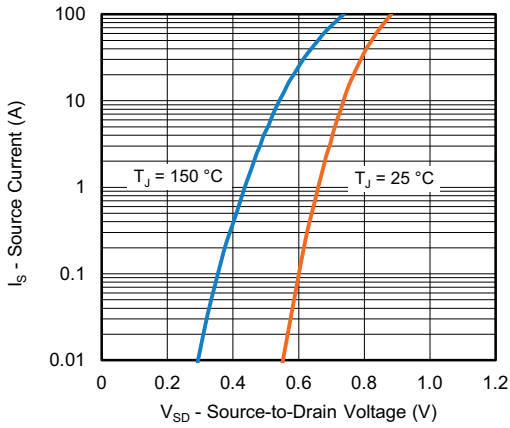
Gate Charge



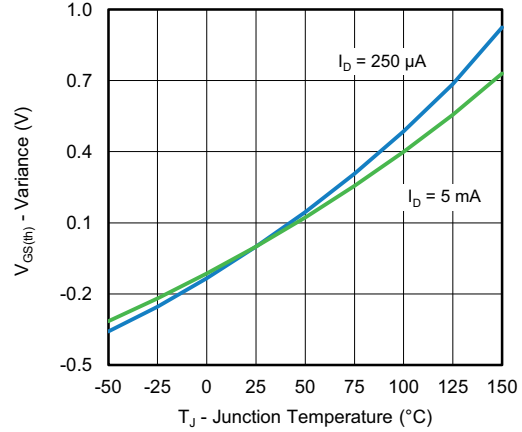
On-Resistance vs. Junction Temperature



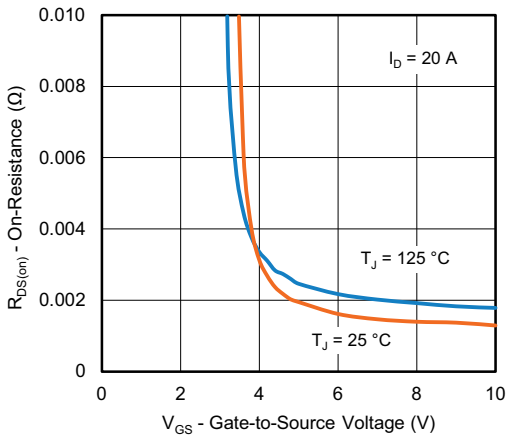
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



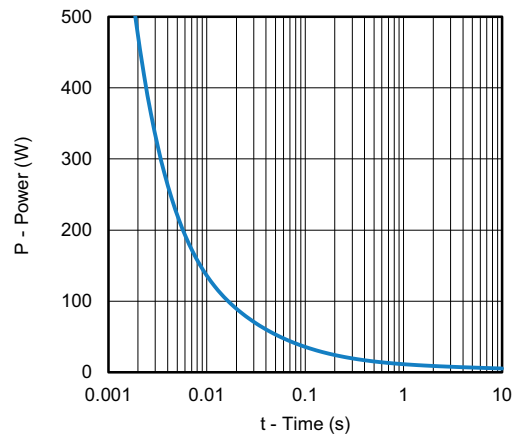
**Source-Drain Diode Forward Voltage**



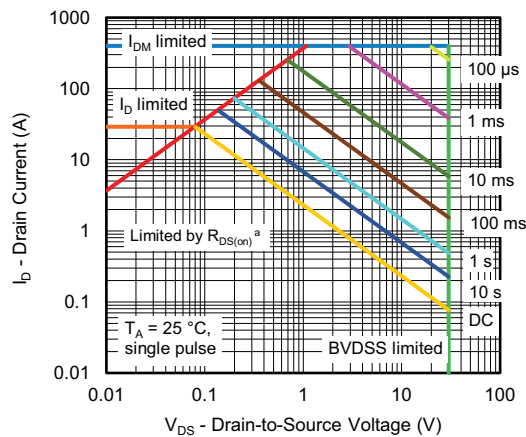
**Threshold Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**Single Pulse Power, Junction-to-Ambient**



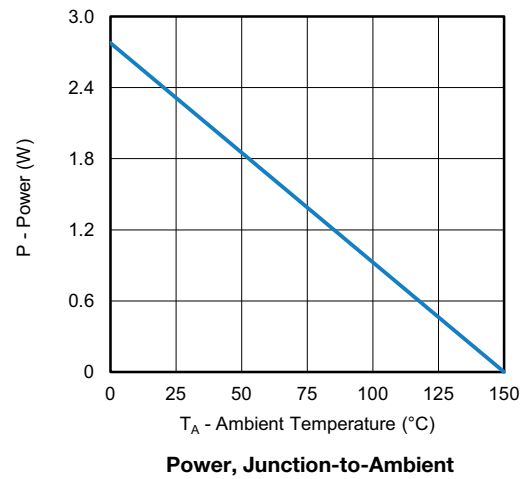
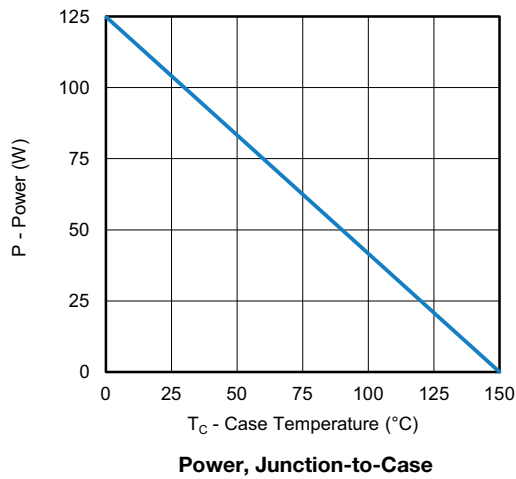
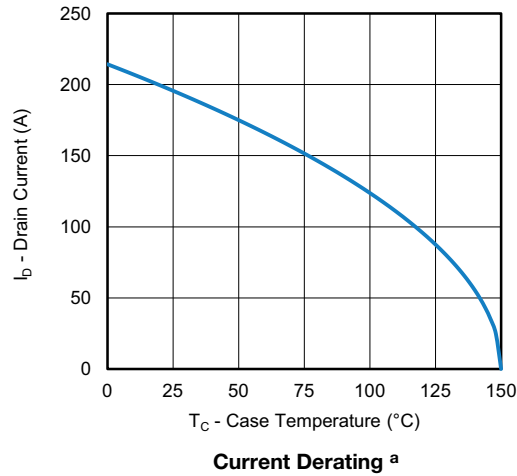
**Safe Operating Area, Junction-to-Ambient**

**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

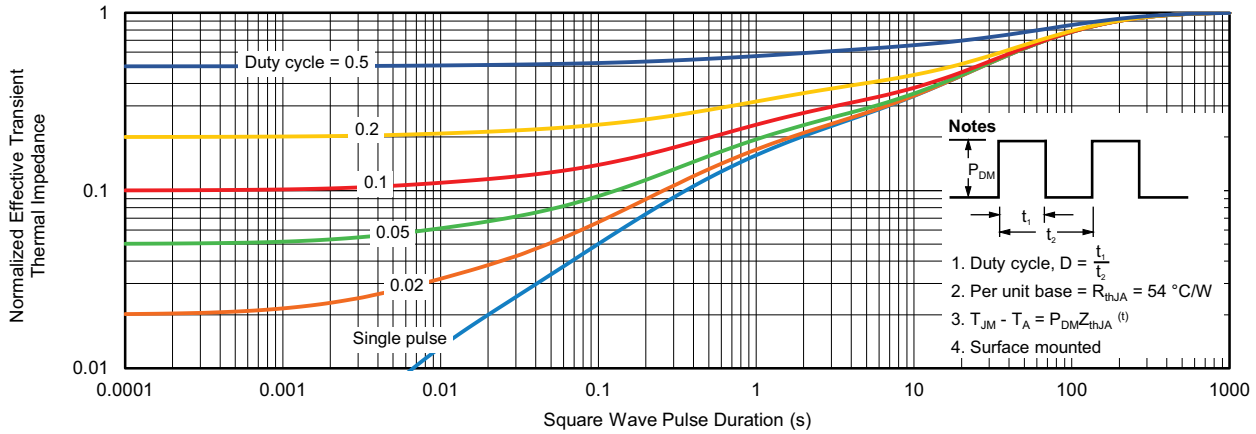


**Note**

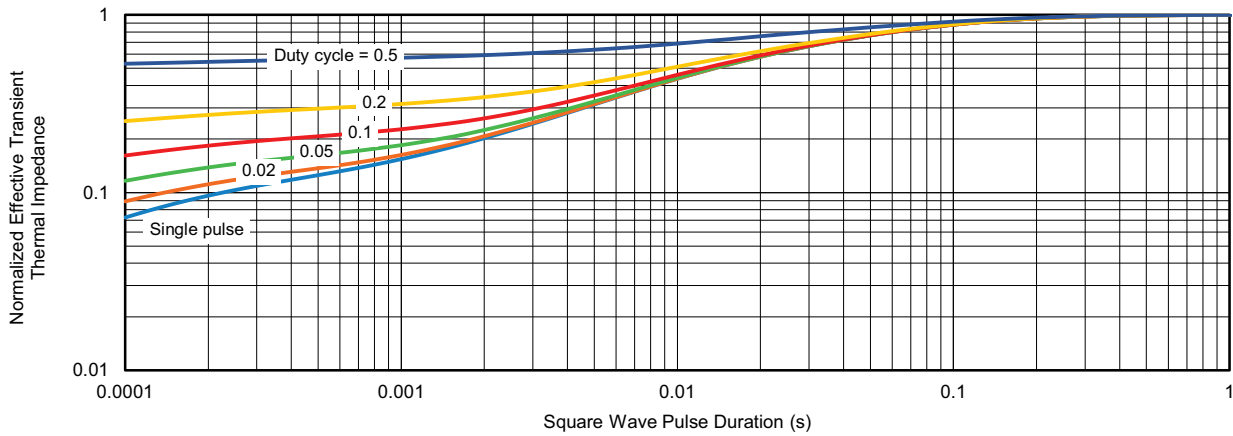
- a. The power dissipation  $P_D$  is based on  $T_{J \text{ max.}} = 150 \text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

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# PowerPAK<sup>®</sup> SO-8, (Single/Dual)



- Notes**
1. Inch will govern.
  2. Dimensions exclusive of mold gate burrs.
  3. Dimensions exclusive of mold flash and cutting burrs.

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.97	1.04	1.12	0.038	0.041	0.044
A1		-	0.05	0	-	0.002
b	0.33	0.41	0.51	0.013	0.016	0.020
c	0.23	0.28	0.33	0.009	0.011	0.013
D	5.05	5.15	5.26	0.199	0.203	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.56	3.76	3.91	0.140	0.148	0.154
D3	1.32	1.50	1.68	0.052	0.059	0.066
D4	0.57 typ.			0.0225 typ.		
D5	3.98 typ.			0.157 typ.		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	5.79	5.89	5.99	0.228	0.232	0.236
E2	3.48	3.66	3.84	0.137	0.144	0.151
E3	3.68	3.78	3.91	0.145	0.149	0.154
E4	0.75 typ.			0.030 typ.		
e	1.27 BSC			0.050 BSC		
K	1.27 typ.			0.050 typ.		
K1	0.56	-	-	0.022	-	-
H	0.51	0.61	0.71	0.020	0.024	0.028
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 typ.			0.005 typ.		
ECN: S17-0173-Rev. L, 13-Feb-17						
DWG: 5881						

## RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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